

Data Sheet

HAL[®] 202

Hall-Effect Sensor

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1. Introduction

The HAL202 Hall switch is produced in CMOS technology. The sensor includes a temperature-compensated Hall plate with active offset compensation, a comparator, and an open-drain output transistor. The comparator compares the actual magnetic flux through the Hall plate (Hall voltage) with the fixed reference values (switching points). Accordingly, the output transistor is switched on or off.

The active offset compensation leads to magnetic parameters which are robust against mechanical stress effects. In addition, the magnetic characteristics are constant in the full supply voltage and temperature range.

The sensor is designed for industrial and automotive applications and operates with supply voltages from 3.8 V to 24 V in the junction temperature range from -40 °C up to 170 °C.

The HAL202 is available in the SMD package SOT89B-3 and in the leaded versions TO92UA-5 and TO92UA-6.

1.1. Features

- switching offset compensation
- operates from 3.8 V to 24 V supply voltage
- operates with static magnetic fields and dynamic magnetic fields up to 10 kHz
- overvoltage protection at all pins
- reverse-voltage protection at V_{DD} -pin
- magnetic characteristics are robust against mechanical stress effects
- short-circuit protected open-drain output by thermal shut down
- constant switching points over a wide supply voltage and temperature range
- the decrease of magnetic flux density caused by rising temperature in the sensor system is compensated by a built-in negative temperature coefficient of the magnetic characteristics
- superior temperature stability for automotive or industrial applications
- high ESD rating
- EMC corresponding to ISO 7637

1.2. Type Description

Latching Sensors:

The sensor has a latching behavior and require a magnetic north and south pole for correct functioning. The output turns low with the magnetic south pole on the branded side of the package and turns high with the magnetic north pole on the branded side. The output does not change if the magnetic field is removed. For changing the output state, the opposite magnetic field polarity must be applied.

1.3. Marking Code

All Hall sensors have a marking on the package surface (branded side). This marking includes the name of the sensor and the temperature range.

Type	Temperature Range
	A
HAL202	202A

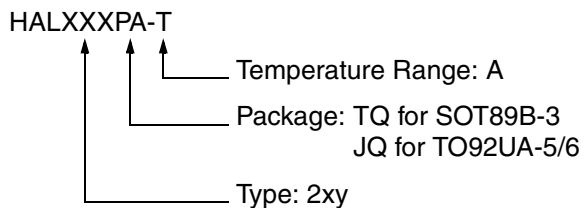
1.4. Operating Junction Temperature Range

The Hall sensors from Micronas are specified to the chip temperature (junction temperature T_J).

A: $T_J = -40\text{ °C to }+170\text{ °C}$

Note: Due to power dissipation, there is a difference between the ambient temperature (T_A) and junction temperature. Please refer to section 4.1. on page 13 for details.

Hall Sensor Package Codes



Example: **HAL202JQ-A**

- Type: 202
- Package: TO92UA-6
- Temperature Range: $T_J = -40\text{ °C to }+170\text{ °C}$

Hall sensors are available in a wide variety of packaging versions and quantities. For more detailed information, please refer to the brochure: “Hall Sensors. Ordering Codes, Packaging, Handling”.

1.5. Solderability and Welding

During soldering reflow processing and manual reworking, a component body temperature of 260 °C should not be exceeded.

Device terminals shall be compatible with laser and electrical welding. Please, note that the success of the welding process is subject to different welding parameters which will vary according to the welding technique used. A very close control of the welding parameters is absolutely necessary in order to reach satisfying results. Micronas, therefore, does not give any implied or express warranty as to the ability to weld the component.

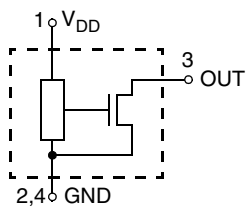


Fig. 1-1: Pin configuration

2. Functional Description

The Hall effect sensor is a monolithic integrated circuit that switches in response to magnetic fields. If a magnetic field with flux lines perpendicular to the sensitive area is applied to the sensor, the biased Hall plate forces a Hall voltage proportional to this field. The Hall voltage is compared with the actual threshold level in the comparator. The temperature-dependent bias increases the supply voltage of the Hall plates and adjusts the switching points to the decreasing induction of magnets at higher temperatures. If the magnetic field exceeds the threshold levels, the open drain output switches to the appropriate state. The built-in hysteresis eliminates oscillation and provides switching behavior of output without bouncing.

Magnetic offset caused by mechanical stress is compensated for by using the “switching offset compensation technique”. Therefore, an internal oscillator provides a two phase clock. The Hall voltage is sampled at the end of the first phase. At the end of the second phase, both sampled and actual Hall voltages are averaged and compared with the actual switching point. Subsequently, the open drain output switches to the appropriate state. The time from crossing the magnetic switching level to switching of output can vary between zero and $1/f_{osc}$.

Shunt protection devices clamp voltage peaks at the Output-pin and V_{DD} -pin together with external series resistors. Reverse current is limited at the V_{DD} -pin by an internal series resistor up to -15 V . No external reverse protection diode is needed at the V_{DD} -pin for reverse voltages ranging from 0 V to -15 V .

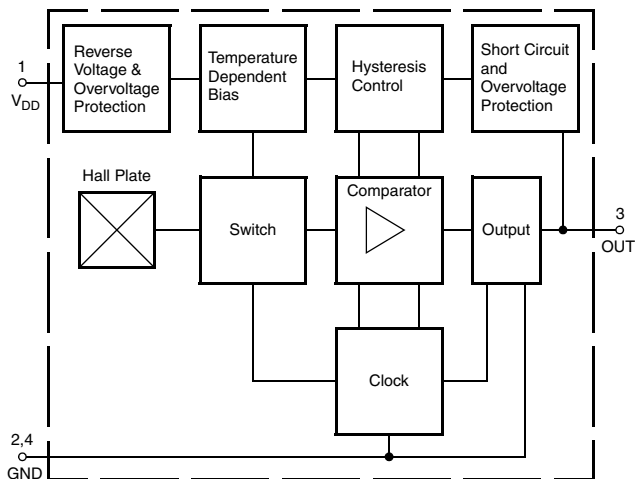


Fig. 2-1: HAL202 block diagram

3. Specifications

3.1. Outline Dimensions

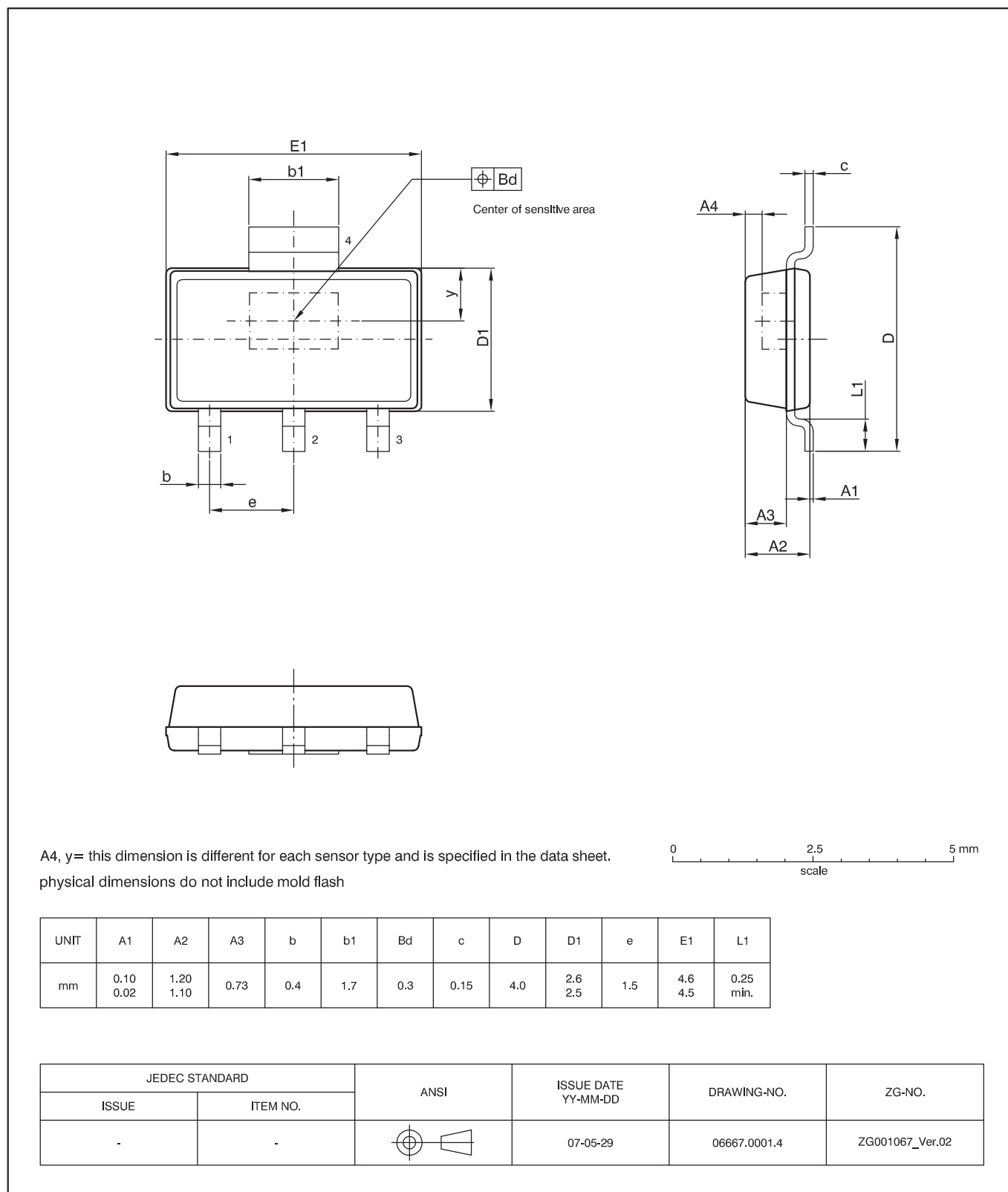


Fig. 3-1:
SOT89B-3: Plastic **S**mall **O**utline **T**ransistor package, 4 leads, with one sensitive area
Weight approximately 0.034 g.

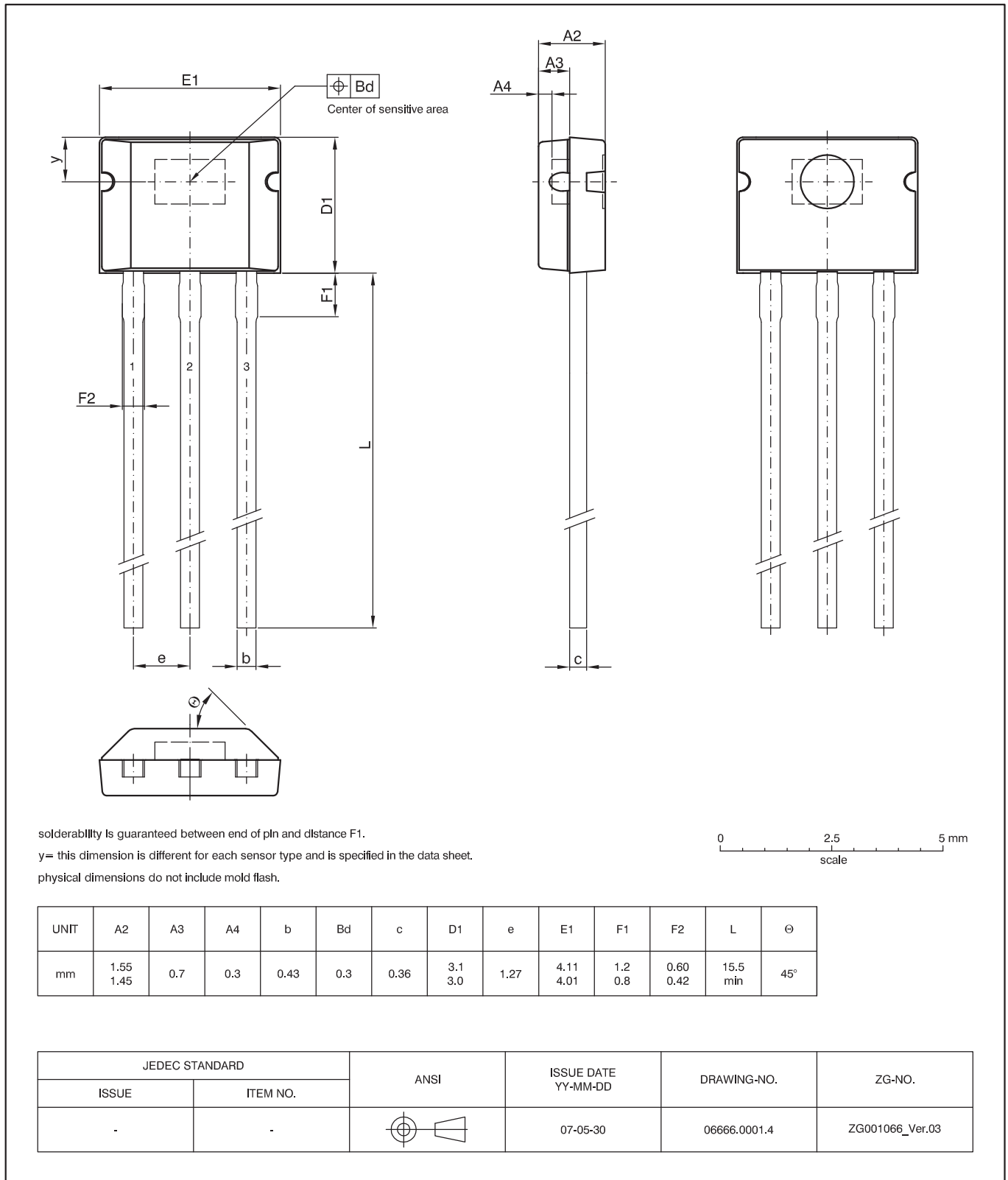


Fig. 3-2:
TO92UA-6: Plastic Transistor Standard UA package, 3 leads
 Weight approximately 0.106 g

3.2. Dimensions of Sensitive Area

0.25 mm × 0.12 mm (on chip)

3.3. Positions of Sensitive Areas

	SOT89B-3	TO92UA-5/6
y	0.95 mm nominal	1.08 mm nominal
A4	0.33 mm nominal	0.30 mm nominal

3.4. Absolute Maximum Ratings

Stresses beyond those listed in the “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these conditions is not implied. Exposure to absolute maximum rating conditions for extended periods will affect device reliability.

This device contains circuitry to protect the inputs and outputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than absolute maximum-rated voltages to this high-impedance circuit.

All voltages listed are referenced to ground (GND).

Symbol	Parameter	Pin Name	Min.	Max.	Unit
V _{DD}	Supply Voltage	1	-15	28 ¹⁾	V
V _O	Output Voltage	3	-0.3	28 ¹⁾	V
I _O	Continuous Output On Current	3	-	50 ¹⁾	mA
¹⁾ as long as T _{J,max} is not exceeded					

3.4.1. Storage and Shelf Life

The permissible storage time (shelf life) of the sensors is unlimited, provided the sensors are stored at a maximum of 30 °C and a maximum of 85% relative humidity. At these conditions, no Dry Pack is required.

Solderability is guaranteed for one year from the date code on the package.

3.5. Recommended Operating Conditions

Functional operation of the device beyond those indicated in the “Recommended Operating Conditions/Characteristics” is not implied and may result in unpredictable behavior, reduce reliability and lifetime of the device.

All voltages listed are referenced to ground (GND).

Symbol	Parameter	Pin Name	Min.	Max.	Unit	Conditions
V _{DD}	Supply Voltage	1	3.8	24	V	
I _O	Continuous Output on Current	3	0	20	mA	
V _O	Output Voltage (output switched off)	3	0	24	V	
T _J	Junction temperature range ¹⁾	-	-40	125	°C	t < 8000 h (not additive)
			-40	140	°C	t < 2000 h (not additive)
			-40	170	°C	t < 1000 h (not additive)

1) Depends on the temperature profile of the application. Please contact Micronas for life time calculations.

3.6. Characteristics

at T_J = -40 °C to +170 °C, V_{DD} = 3.8 V to 24 V, GND = 0 V

at Recommended Operation Conditions if not otherwise specified in the column “Conditions”.

Typical Characteristics for T_J = 25 °C and V_{DD} = 12 V.

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit	Conditions
I _{DD}	Supply Current over Temperature Range	1	1.6	3	5.2	mA	
V _{DDZ}	Overvoltage Protection at Supply	1	-	28.5	32	V	I _{DD} = 25 mA, T _J = 25 °C, t = 20 ms
V _{OZ}	Overvoltage Protection at Output	3	-	28	32	V	I _{OH} = 25 mA, T _J = 25 °C, t = 20 ms
V _{OL}	Output Voltage over Temperature Range	3	-	130	400	mV	I _{OL} = 20 mA
I _{OH}	Output Leakage Current over Temperature Range	3	-	-	10	µA	Output switched off, T _J ≤ 150 °C, V _{OH} = 3.8 to 24
f _{osc}	Internal Oscillator Chopper Frequency over Temperature Range	-	-	62	-	kHz	
t _{en(O)}	Enable Time of Output after Setting of V _{DD}	1	-	35	-	µs	V _{DD} = 12 V
t _r	Output Rise Time	3	-	75	400	ns	V _{DD} = 12 V, R _L = 820 Ohm, C _L = 20 pF
t _f	Output Fall Time	3	-	50	400	ns	
SOT89B Package							
R _{thja}	Thermal Resistance Junction to Ambient	-	-	-	212	K/W	Measured with a 1s0p board 30 mm x 10 mm x 1.5 mm, pad size (see Fig. 3-3)
R _{thjc}	Junction to Case	-	-	-	73	K/W	

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit	Conditions
TO92UA Package							
R_{thja}	Thermal Resistance Junction to Ambient	–	–	–	225	K/W	Measured with a 1s0p board
R_{thjc}	Junction to Case	–	–	–	63	K/W	

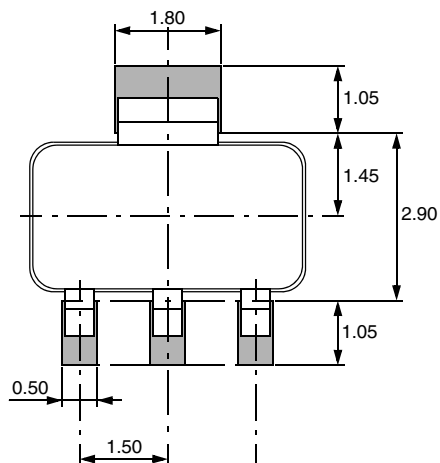
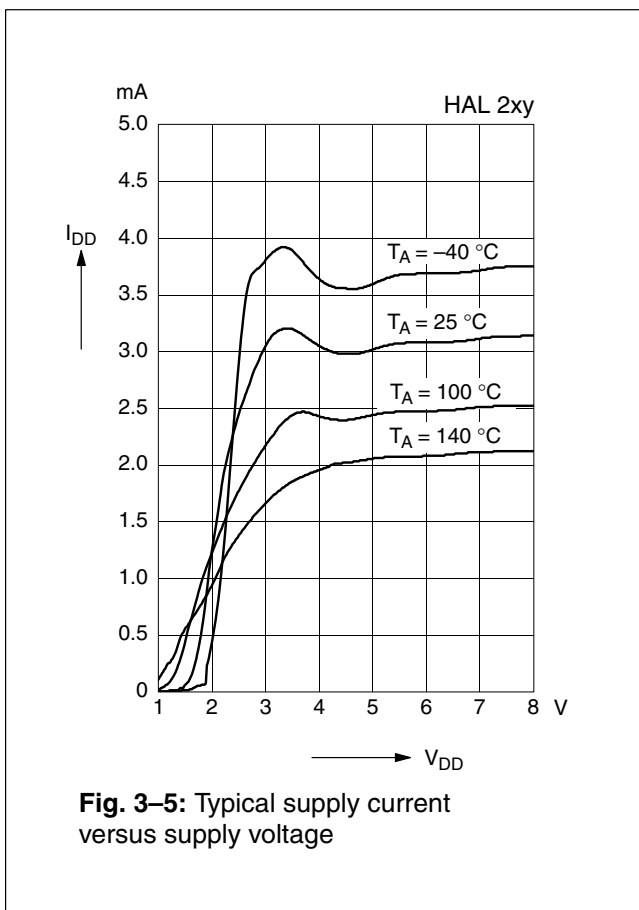
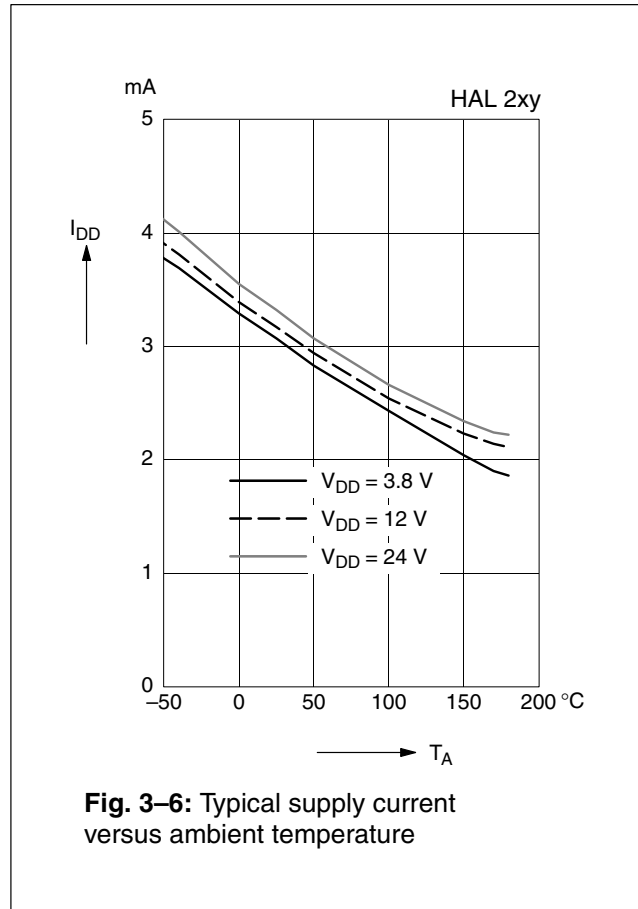
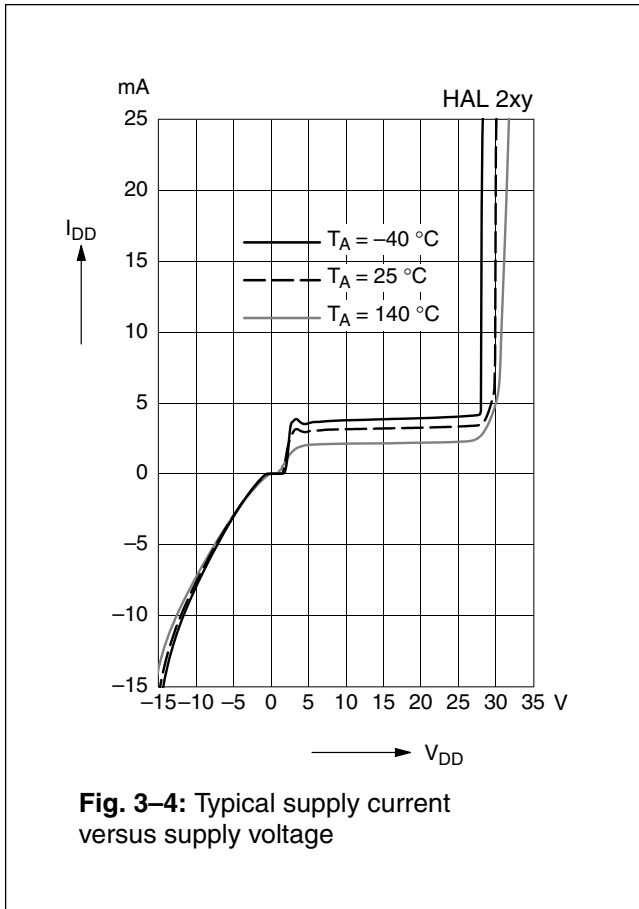


Fig. 3–3: Recommended footprint SOT89B-3, Dimensions in mm
All dimensions are for reference only. The pad size may vary depending on the requirements of the soldering process.

3.7. Magnetic Characteristics Overview

at $T_J = -40\text{ °C}$ to $+170\text{ °C}$, $V_{DD} = 3.8\text{ V}$ to 24 V ,
Typical Characteristics for $V_{DD} = 12\text{ V}$. Magnetic flux density values of switching points.
Positive flux density values refer to the magnetic south pole at the branded side of the package.

Sensor Switching Type	Parameter T_J	On point B_{ON}			Off point B_{OFF}			Hysteresis B_{HYS}			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
HAL202 latching	-40 °C	0.5	2.8	6.5	-6.5	-2.8	-0.5	–	5.6	–	mT
	25 °C	0.5	2.6	6	-6	-2.6	-0.5	–	5.2	–	mT
	140 °C	0.1	2.4	5.5	-5.5	-2.4	-0.1	–	4.8	–	mT
	170 °C	0.1	2.4	5.5	-5.5	-2.4	-0.1	–	4.8	–	mT



4. Application Notes

4.1. Ambient Temperature

Due to the internal power dissipation, the temperature on the silicon chip (junction temperature T_J) is higher than the temperature outside the package (ambient temperature T_A).

$$T_J = T_A + \Delta T$$

At static conditions and continuous operation, the following equation applies:

$$\Delta T = I_{DD} \times V_{DD} \times R_{th}$$

If $I_{OUT} > I_{DD}$, please contact Micronas application support for detailed instructions on calculating ambient temperature.

For typical values, use the typical parameters. For worst case calculation, use the max. parameters for I_{DD} and R_{th} , and the max. value for V_{DD} from the application.

For all sensors, the junction temperature range T_J is specified. The maximum ambient temperature T_{Amax} can be calculated as:

$$T_{Amax} = T_{Jmax} - \Delta T$$

4.2. Operation

4.2.1. Extended Operating Conditions

All HAL202-sensors fulfill the electrical and magnetic characteristics when operated within the Recommended Operating Conditions (see page 10).

Supply Voltage Below 3.8 V

Typically, the sensor operates with supply voltages above 3 V, however, below 3.8 V some characteristics may be outside the specification.

Note: The functionality of the sensor below 3.8 V is not tested. For special test conditions, please contact Micronas.

4.2.2. Start-up Behavior

Due to the active offset compensation, the sensor has an initialization time (enable time $t_{en(O)}$) after applying the supply voltage. The parameter $t_{en(O)}$ is specified in Section 3.6.: Characteristics on page 10.

During the initialization time, the output state is not defined and the output can toggle. After $t_{en(O)}$, the output will be low if the applied magnetic field B is above B_{ON} . The output will be high if B is below B_{OFF} .

For magnetic fields between B_{OFF} and B_{ON} , the output state of the HAL sensor after applying V_{DD} will be either low or high. In order to achieve a well-defined output state, the applied magnetic field must be above B_{ONmax} , respectively, below B_{OFFmin} .

4.3. EMC and ESD

For applications with disturbances on the supply line or radiated disturbances, a series resistor and a capacitor are recommended (see Fig. 4–1). The series resistor and the capacitor should be placed as closely as possible to the HAL sensor.

Applications with this arrangement passed the EMC tests according to the product standards ISO 7637.

Please contact Micronas for the detailed investigation reports with the EMC and ESD results.

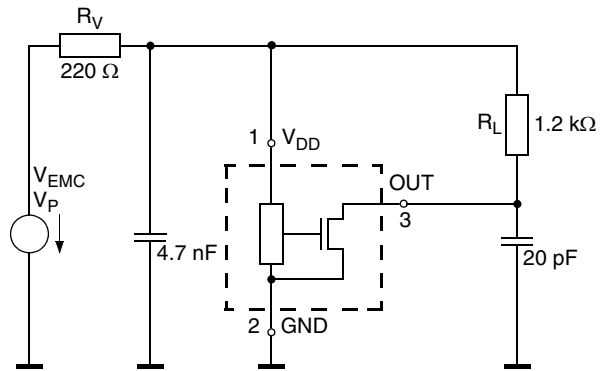


Fig. 4–1: Test circuit for EMC investigation

5. Data Sheet History

1. Data Sheet: "HAL202 Hall-Effect Sensor", July 21, 2011, DSH000159_001EN. First release of the data sheet.